

10/708,907

[0001] The present application is related to a new U.S. Patent Application Serial No. 10/708,586, filed concurrently on March 12, 2004 to Clark et al Edward J. Nowak, entitled "High-Performance CMOS SOI Devices on Hybrid Crystal-Oriented Substrates", having (IBM) Docket No. BUR920030159US1, assigned to the present assignee, and incorporated herein by reference.

[0074] Another method of forming an integrated circuit structure is shown in Figures 8A-8H. This embodiment is directed toward forming FinFETs type transistors with different types of crystalline orientations. As shown in Figure 8A, this embodiment begins by forming a first insulator 804 on a first substrate structure 800 with a first crystalline orientation. Next, the invention bonds a second substrate structure 806 having a second crystalline orientation to the first insulator 804 to form the laminated structure shown in Figure 8A. An additional insulator 800 802 can be formed any time during this process.